

IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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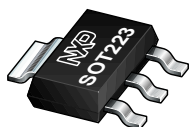
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Thank you for your cooperation and understanding,

WeEn Semiconductors



BT168GWF

SCR

11 July 2014

Product data sheet

1. General description

Planar passivated SCR with faster switching performance and sensitive gate in a SOT223 surface mounted plastic package. This SCR with enhanced commutation performance is also designed to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Fast commutation performance for higher frequency operation
- Full wave rectified AC applications
- Sensitive gate
- Direct triggering from microcontrollers, low power drivers and logic ICs

3. Applications

- Earth leakage circuit breakers (ELCB/GFI)
- Ignition circuits (gas appliances, small engines and HID lighting)

4. Quick reference data

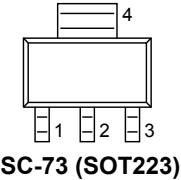
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5	-	-	8	A
$I_{T(AV)}$	average on-state current	half sine wave; $T_{sp} \leq 112\text{ }^{\circ}\text{C}$; Fig. 1	-	-	0.63	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{sp} \leq 112\text{ }^{\circ}\text{C}$; Fig. 2 ; Fig. 3	-	-	1	A
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 10\text{ mA}$; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 9	70	200	450	μA



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 SC-73 (SOT223)	 sym037
2	A	anode		
3	G	gate		
4	mb	mb; connected to anode		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT168GWF	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
V_{RRM}	repetitive peak reverse voltage		-	600	V
$I_{\text{T(AV)}}$	average on-state current	half sine wave; $T_{\text{sp}} \leq 112\text{ }^{\circ}\text{C}$; Fig. 1	-	0.63	A
$I_{\text{T(RMS)}}$	RMS on-state current	half sine wave; $T_{\text{sp}} \leq 112\text{ }^{\circ}\text{C}$; Fig. 2 ; Fig. 3	-	1	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 10\text{ ms}$; Fig. 4 ; Fig. 5	-	8	A
		half sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 8.3\text{ ms}$	-	9	A
I^2t	I^2t for fusing	$t_{\text{p}} = 10\text{ ms}$; SIN	-	0.32	A^2s
di_{T}/dt	rate of rise of on-state current	$I_{\text{T}} = 2\text{ A}$; $I_{\text{G}} = 10\text{ mA}$; $di_{\text{G}}/dt = 100\text{ mA}/\mu\text{s}$	-	50	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	1	A
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	2	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.1	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_{j}	junction temperature		-	125	$^{\circ}\text{C}$

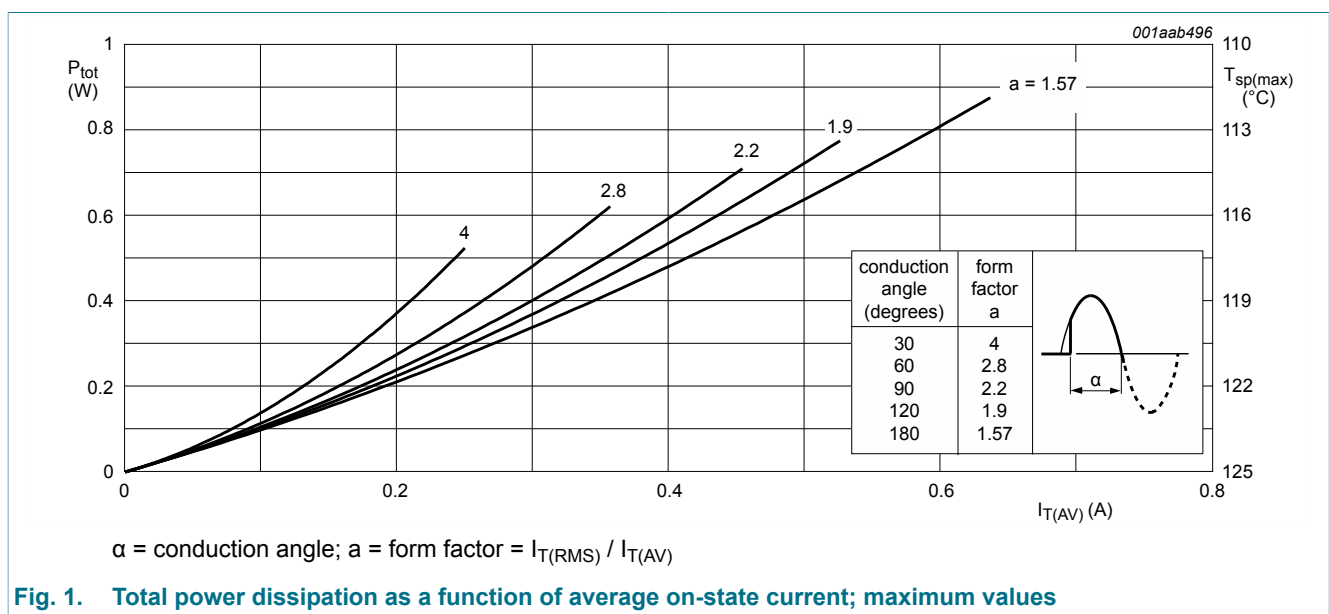


Fig. 1. Total power dissipation as a function of average on-state current; maximum values

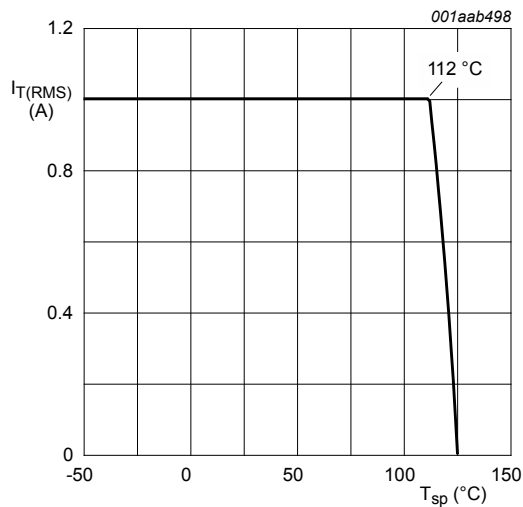
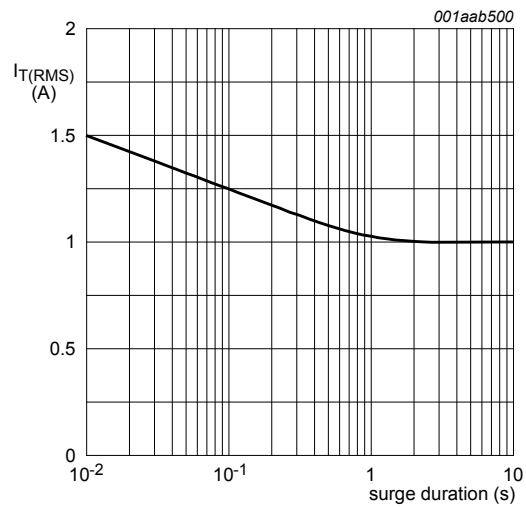
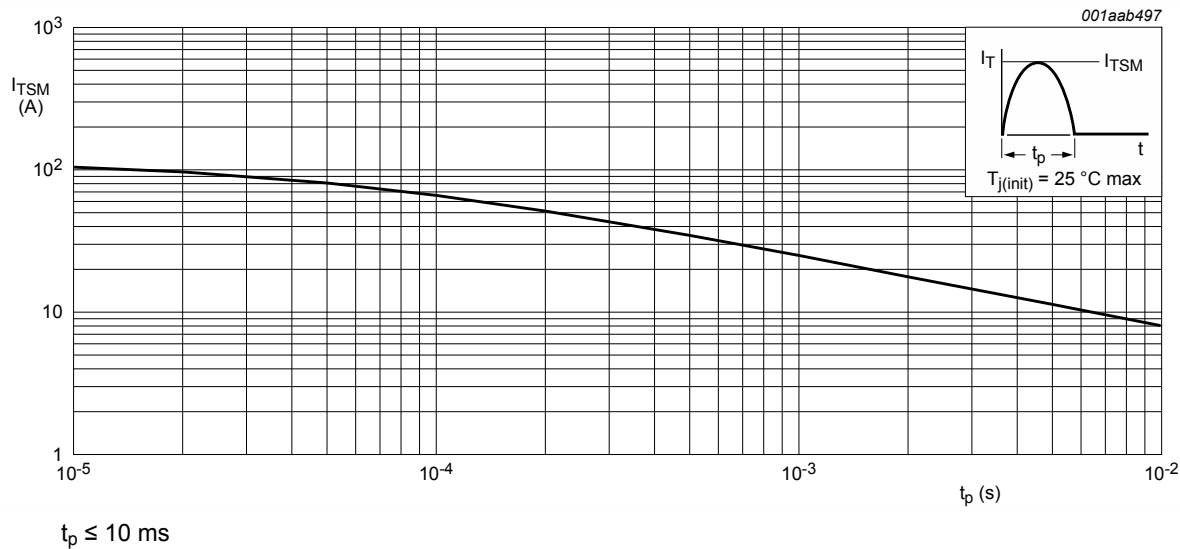


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values



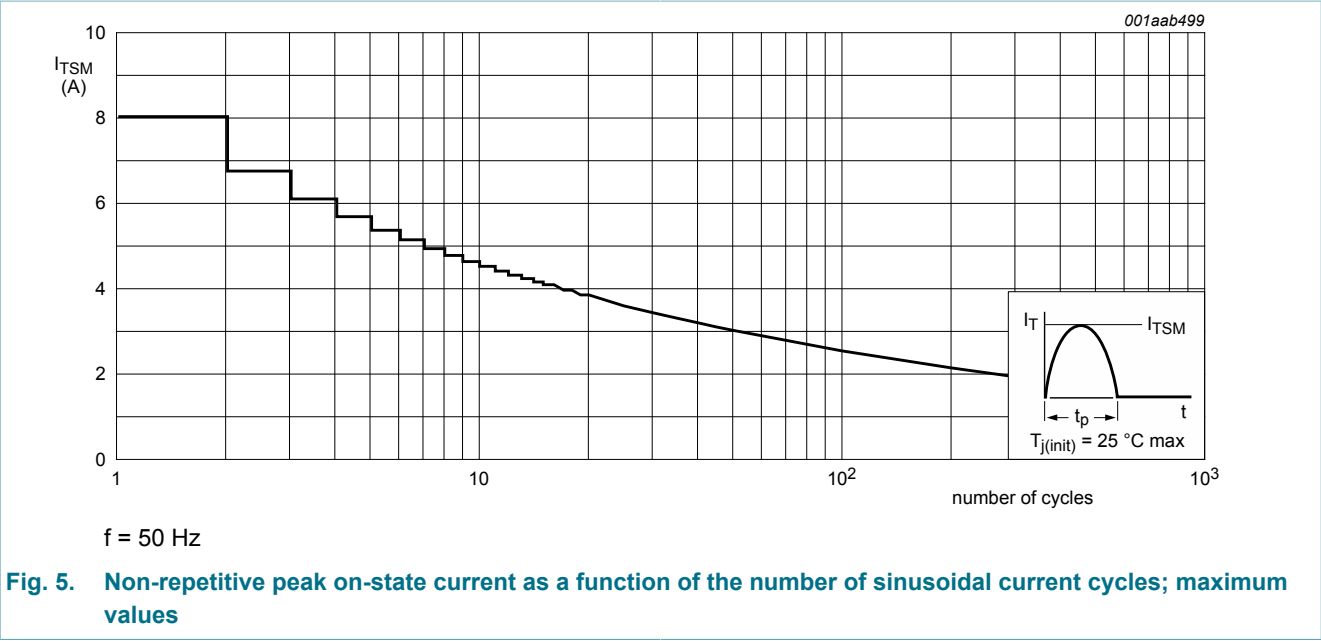
$f = 50 \text{ Hz}; T_{sp} = 112 \text{ °C}$

Fig. 3. RMS on-state current as a function of surge duration; maximum values



$t_p \leq 10 \text{ ms}$

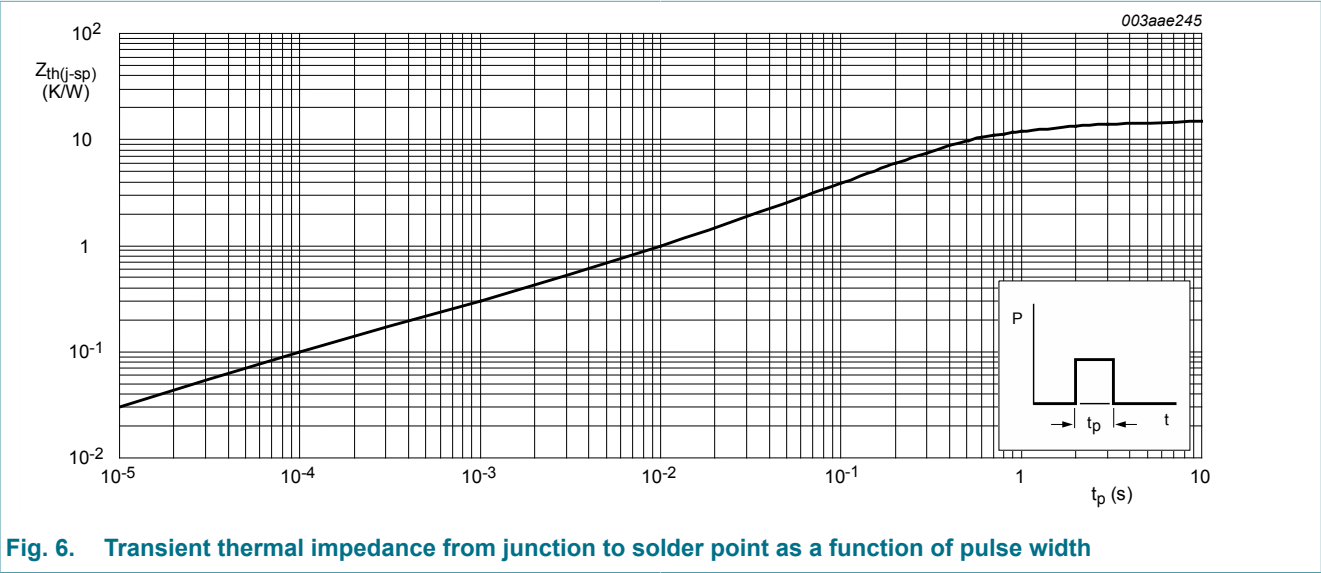
Fig. 4. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

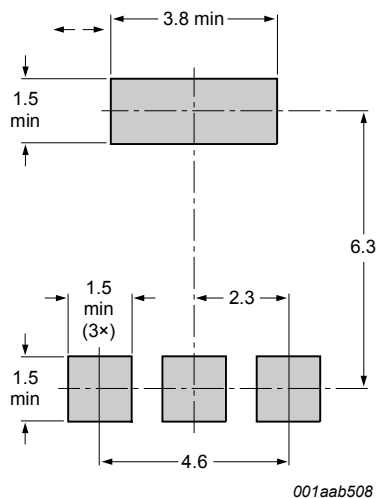


8. Thermal characteristics

Table 5. Thermal characteristics

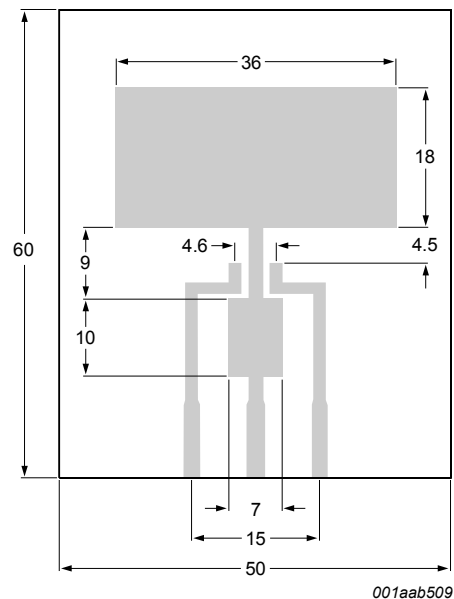
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	Fig. 6	-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed-circuit board mounted; minimum footprint; Fig. 7	-	156	-	K/W
		printed-circuit board mounted; pad area; Fig. 8	-	70	-	K/W





All dimensions are in mm

Fig. 7. Minimum footprint SOT223



All dimensions are in mm

Printed circuit board:

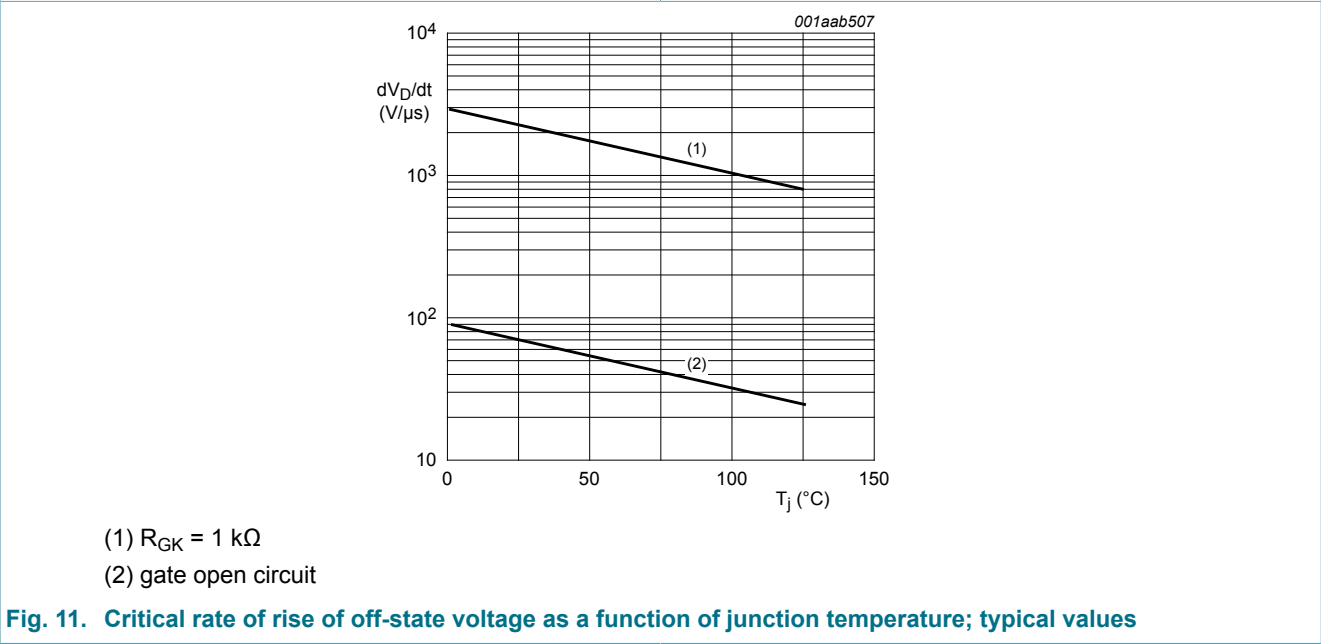
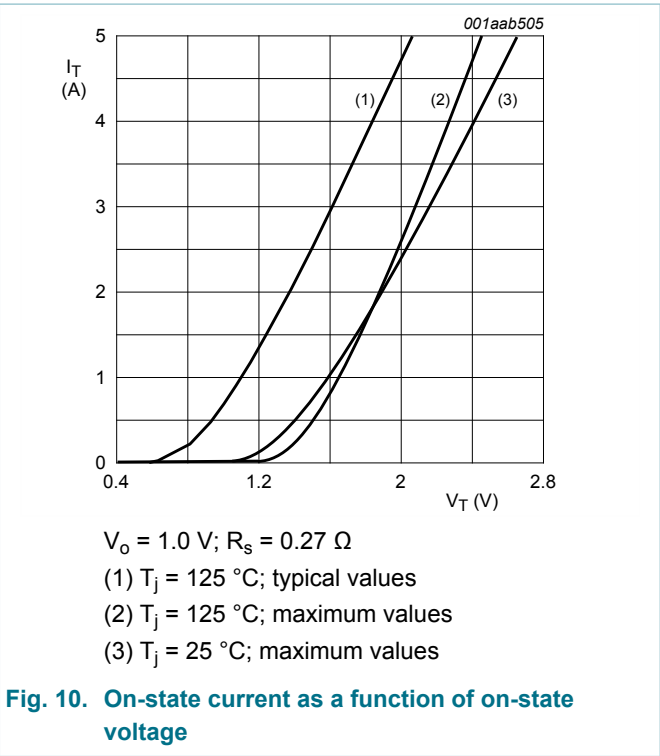
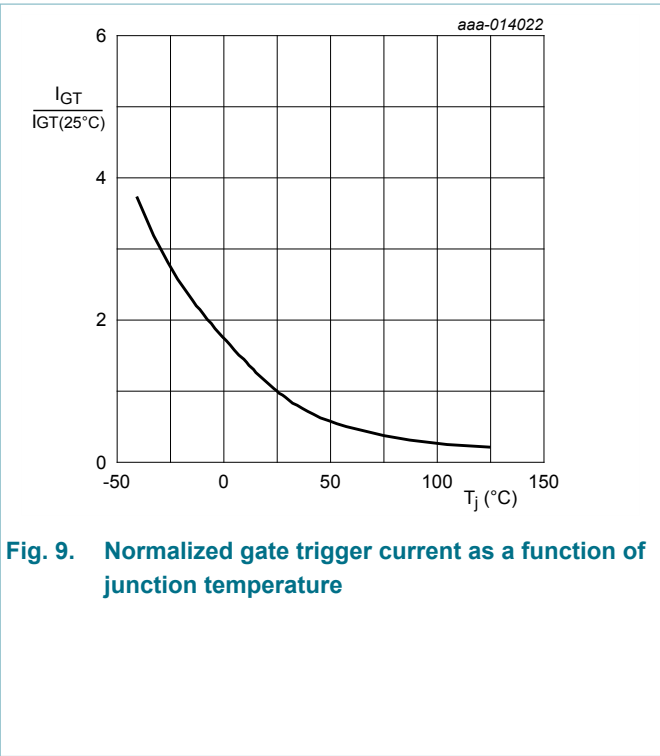
FR4 epoxy glass (1.6 mm thick), copper laminate
(35 µm thick)

Fig. 8. Printed circuit board pad area: SOT223

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 10\text{ mA}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9	70	200	450	μA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.5\text{ mA}$; $R_{GK} = 1\text{ k}\Omega$; $T_j = 25\text{ }^\circ\text{C}$	3	7.5	13	mA
I_H	holding current	$V_D = 12\text{ V}$; $R_{GK} = 1\text{ k}\Omega$; $T_j = 25\text{ }^\circ\text{C}$	0.5	4.1	10	mA
V_T	on-state voltage	$I_T = 1.2\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10	-	1.35	1.7	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 10\text{ mA}$; $T_j = 25\text{ }^\circ\text{C}$	-	0.5	0.8	V
		$V_D = 600\text{ V}$; $I_T = 10\text{ mA}$; $T_j = 125\text{ }^\circ\text{C}$	0.2	0.3	-	V
I_D	off-state current	$V_D = 600\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $R_{GK} = 1\text{ k}\Omega$	-	0.05	0.1	mA
I_R	reverse current	$V_R = 600\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $R_{GK} = 1\text{ k}\Omega$	-	0.05	0.1	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $R_{GK} = 1\text{ k}\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; Fig. 11	350	800	-	V/ μs
		$V_{DM} = 402\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit; Fig. 11	-	25	-	V/ μs



10. Package outline

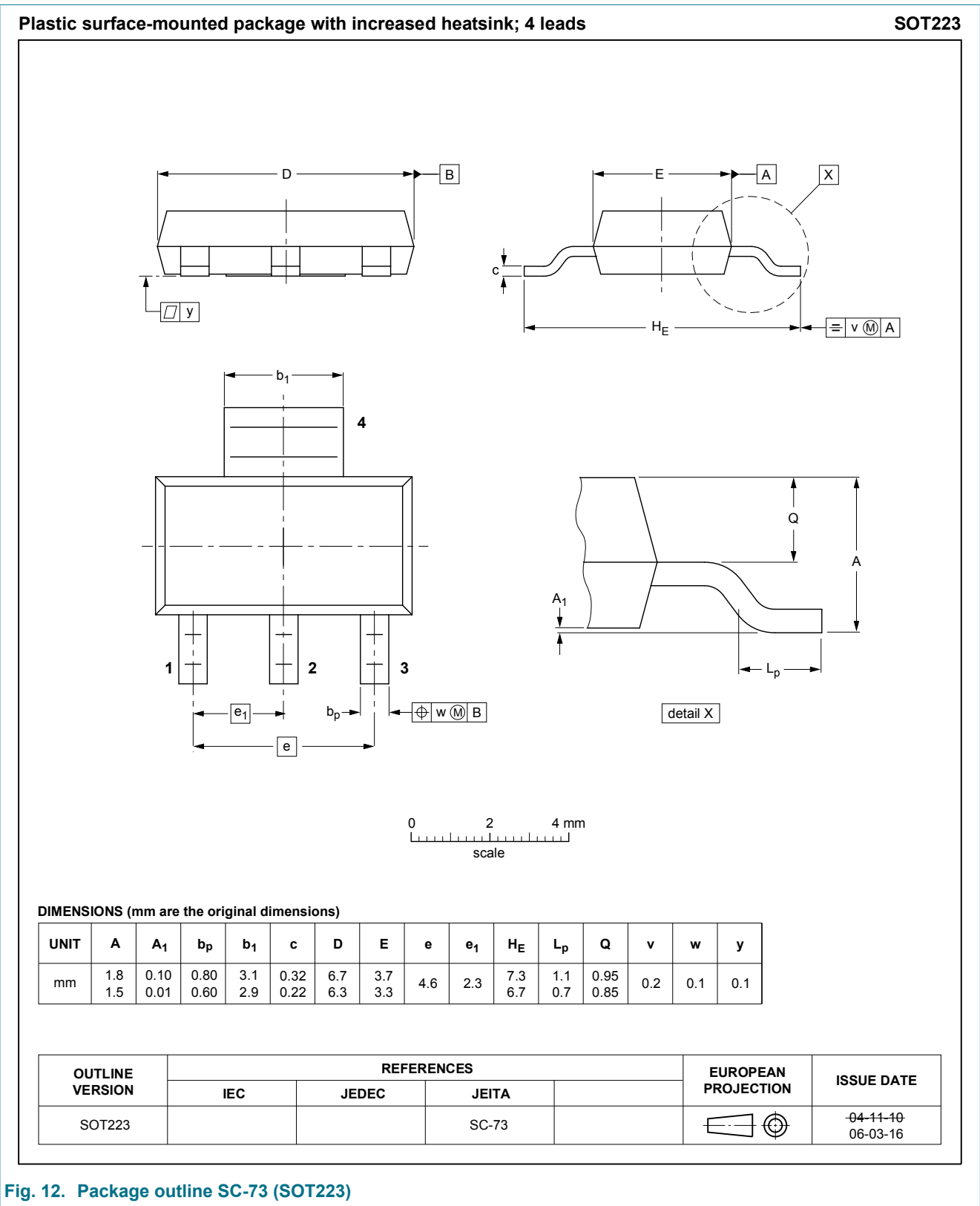


Fig. 12. Package outline SC-73 (SOT223)

11. Legal information

11.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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12. Contents

1 General description 1

2 Features and benefits 1

3 Applications 1

4 Quick reference data 1

5 Pinning information 2

6 Ordering information 2

7 Limiting values 3

8 Thermal characteristics 6

9 Characteristics 8

10 Package outline 10

11 Legal information 11

11.1 Data sheet status 11

11.2 Definitions 11

11.3 Disclaimers 11

11.4 Trademarks 12

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